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monocrystalline material layer selected from the group consisting of GaAs, GaInAs, AlGaAs, Si and AlAs, and wherein said first monocrystalline material layer has a thickness in the range of from about 20 angstroms to about 50 angstroms.

Please cancel Claims 3, 16 and 17-42.

Please add new Claim 43 as follows:

A²
43. (New) The semiconductor structure of claim 2, wherein the monocrystalline oxide is formed of material selected from the group consisting of $\text{Sr}_z\text{Ba}_{1-z}\text{TiO}_3$, $\text{Sr}_z\text{Ba}_{1-z}\text{ZrO}_3$, $\text{Sr}_z\text{Ba}_{1-z}\text{HfO}_3$, $\text{Sr}_z\text{Ba}_{1-z}\text{SnO}_3$ and CaTiO_3 , where z ranges from 0 to approximately 1.

SUPPORT FOR THE AMENDMENTS

The amendment to Claim 1 places original Claim 16 in independent form, and thus places all pending claims in condition for allowance. The claim originally appearing at page 27, lines 18-20, has been presented as new Claim 43. No new matter has been entered.